! "##$%& ' ( )

Rev.A Aug.-2022

' ! ')*+%%!

23 Silicon NPN Digital transistor in a SOT-23 Plastic Package.
)

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing proce pr L e e er i

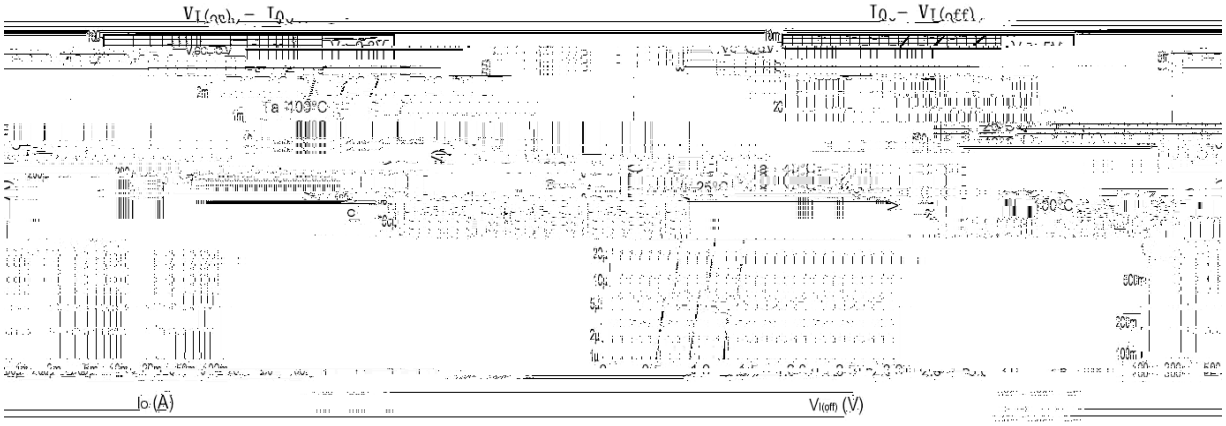
)

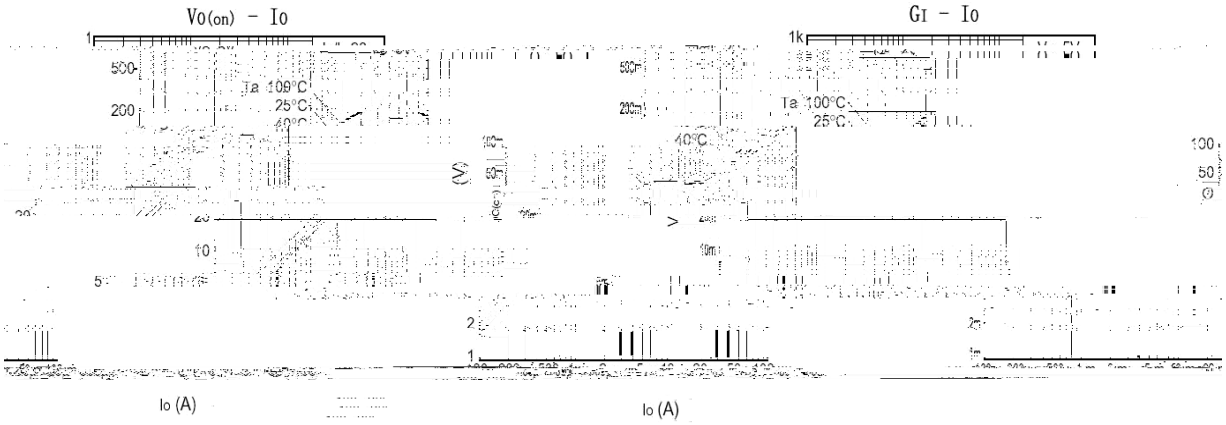
Parameter	Symbol	Rating	Unit
Output Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	40	V
		-10	V
Output Current	I_{CM}	100	mA
	I_O	50	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

)

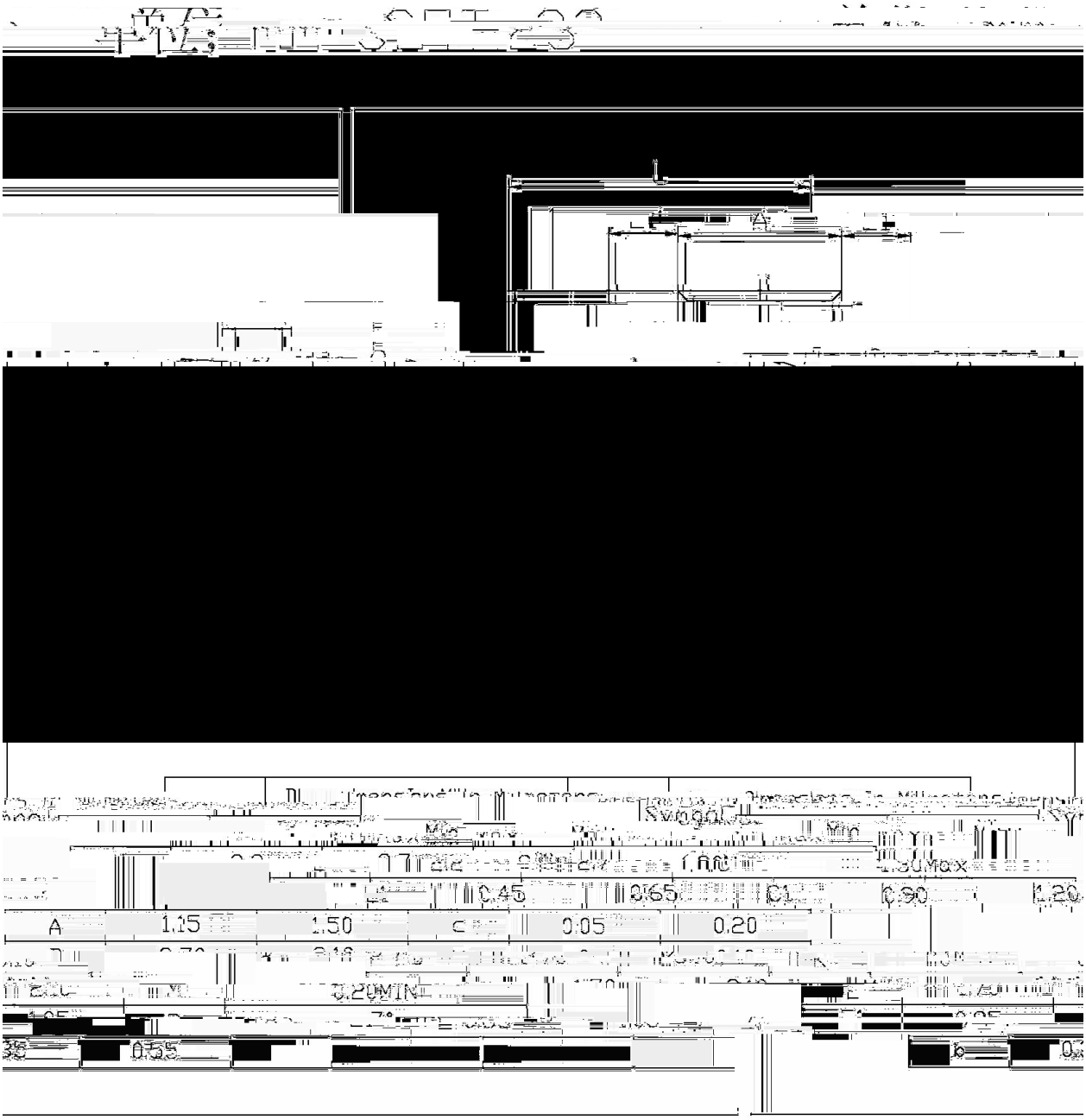
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage	$V_{I(off)}$	V_{CC}=5.0V I_O=100μA			0.5	V
Input Voltage	$V_{I(on)}$	V_O=0.3V I_O=10mA	3			V
Output Voltage	$V_{O(on)}$	I_O=10mA I_I=0.5mA			0.3	V
Input Current	I_I	V_I=5.0V			0.88	mA
Output Cut-off Current	$I_{O(off)}$	V_{CC}=50V V_I=0V			0.5	μA
DC Current Gain	G_I	V_O=5.0V I_O=5.0mA	30			
Transition Frequency	f_T	V_{CE}=10V I_C=5.0mA f=100MHz		250		MHz
Resistance1	R_1		7	10	13	KΩ
Resistance Ratio	R_2/R_1		0.8	1	1.2	

)) ,)) %8 - 3;2/398) " 69293; - 2/0;/3) " B2 . -)





)) ,)) D93?9@-) /H -<0/4<0)



)) ,)) > 92?/<@)ℕ<0;2B3;/4<0)